

MICRO ELECTRONICS

PN3568

NPN

SILICON
TRANSISTOR

PN3568 is NPN silicon planar epitaxial transistor designed for amplifier and switching applications for collector current up to 500mA.

TO-92



EBC

ABSOLUTE MAXIMUM RATINGS

| | | |
|--|-----------------------------------|---------------|
| Collector-Base Voltage | V _{CB0} | 80V |
| Collector-Emitter Voltage | V _{CE0} | 60V |
| Emitter-Base Voltage | V _{EB0} | 5V |
| Collector Current | I _C | 500mA |
| Total Power Dissipation | P _{tot} | 600mW |
| Operating Junction & Storage Temperature | T _j , T _{stg} | -55 to +150°C |

ELECTRICAL CHARACTERISTICS (T_A=25°C)

| PARAMETER | SYMBOL | MIN | MAX | UNIT | TEST CONDITIONS |
|--------------------------------------|----------------------|-----|------|------|---|
| Collector-Base Breakdown Voltage | BV _{CB0} | 80 | | V | I _C =100μA I _E =0 |
| Collector-Emitter Breakdown Voltage | LV _{CE0} | 60 | | V | I _C =10mA I _B =0* |
| Emitter-Base Breakdown Voltage | BV _{EB0} | 5 | | V | I _E =10μA I _C =0 |
| Collector Cutoff Current | I _{CB0} | | 50 | nA | V _{CB} =40V I _E =0 |
| D.C. Current Gain | HFE | 40 | | | I _C =30mA V _{CE} =1V* |
| | | 40 | 120 | | I _C =150mA V _{CE} =1V* |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | | 0.25 | V | I _C =150mA I _B =15mA* |
| Output Capacitance | C _{ob} | | 20 | pF | V _{CB} =10V f=1MHz |
| Current Gain-Bandwidth Product | f _T | 60 | 600 | MHz | I _C =50mA V _{CE} =1V |

* Pulse Test : Pulse Width = 300μS, Duty Cycle = 2%.

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This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.